

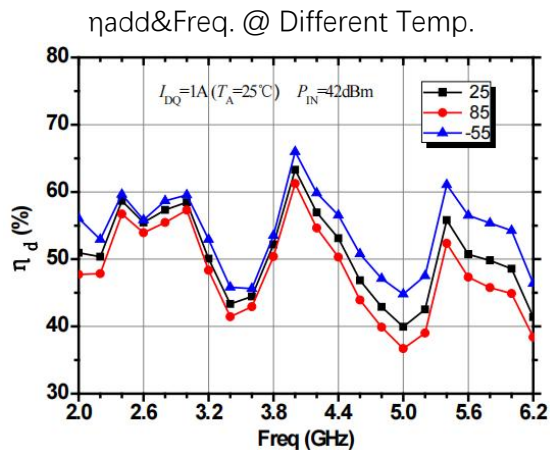
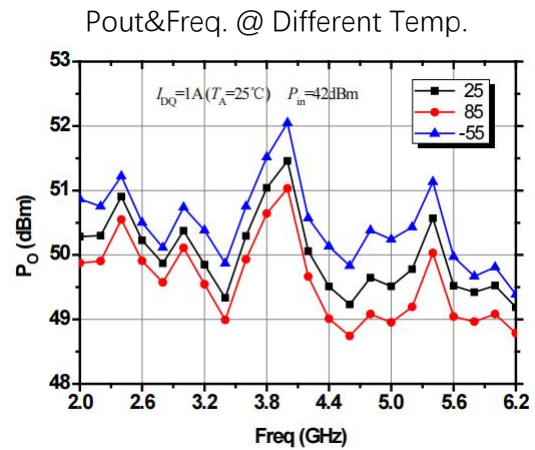
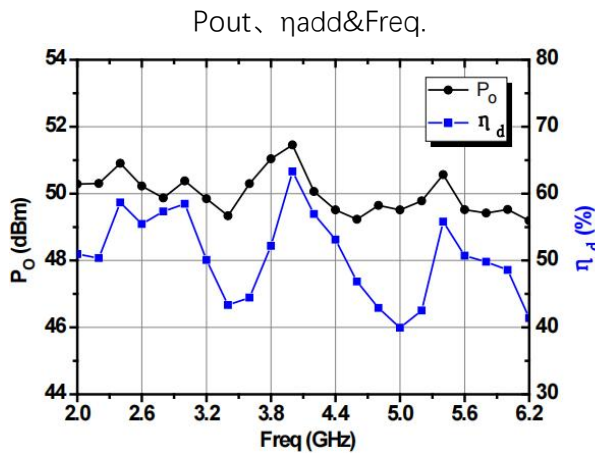
Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 2.0~6.2GHz
- Typical Pout : $\geq 49\text{dBm(CW)}$
- Typical Gain: $\geq 7\text{dB}$
- Typical PAE: $\geq 40\%$
- Bias: 28V@1A
- Package: MoCu Carrier(22.6*24*2mm)

Electrical Specifications (TA=25°C, Vd=28V, Idq=1A, F: 2.0~6.2GHz, Pin=42dBm)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	49	-	-	dBm
Gp	Power Gain	7	-	-	dB
η_{add}	Power Added Efficiency	40	-	-	%
ΔG_p	Gain Flatness	-	-	± 1.0	dB
Rth	Thermal Resistance	-	0.95	-	°C/W

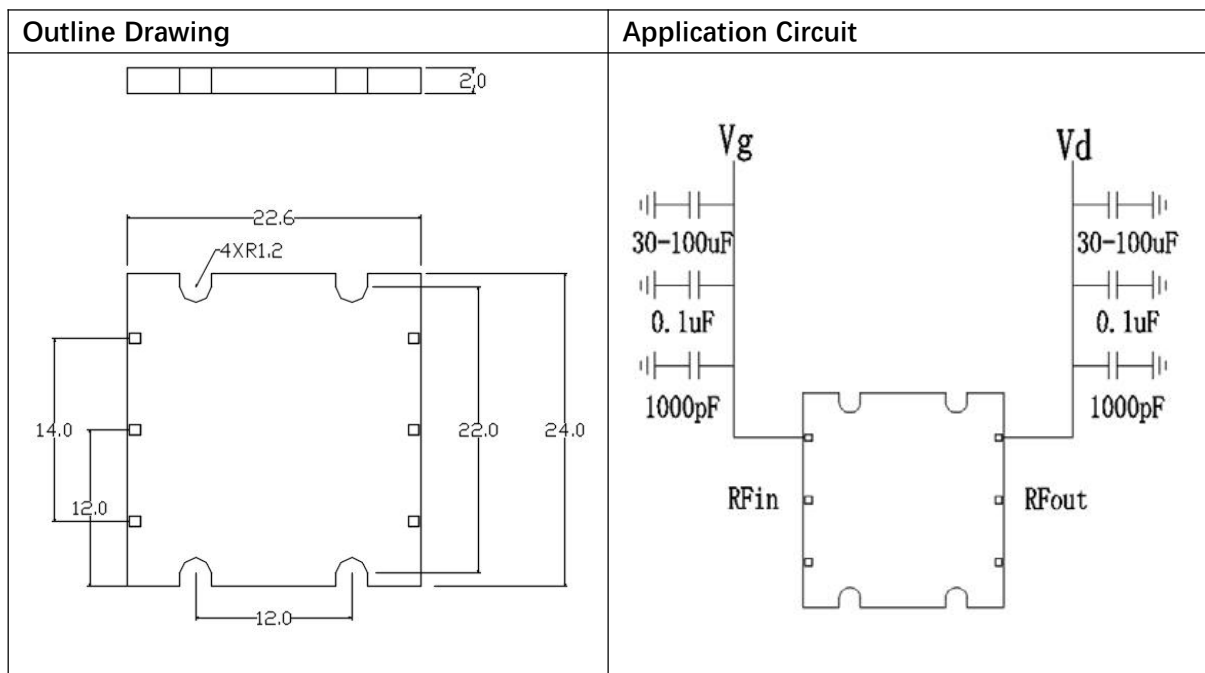
Test Curves



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	36V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	250W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.



Note:

- (1) The typical packaging form is a molybdenum copper carrier, which can change the feeding position and provide a shell package according to customer needs;
- (2) Please strictly follow the sequence of applying negative power first and then positive power. When removing power, first decrease the leakage voltage and then decrease the gate voltage;
- (3) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (4) This product is an electrostatic sensitive device, which requires attention to electrostatic protection during storage and use, and requires good grounding during use;
- (5) The input standing wave ratio is high, and the input terminal needs to adopt radio frequency isolation measures.